

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 30 A, 1200 V, D1, Die

PCFFS30120AF

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature dependent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 361 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery

Applications

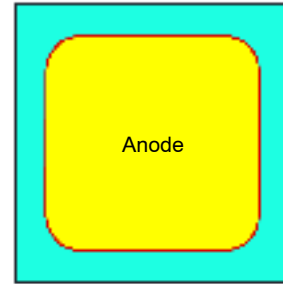
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

Die Information

- Wafer Diameter: 6 inch
- Die Size: 3,700 × 3,700 μm (include Scribe Lane)
- Metallization:
 - ◆ Top Ti/TiN/AlCu 4 μm
 - ◆ Back Ti/NiV/Ag
- Die Thickness: Typ. 200 μm
- Bonding Pad Size
 - ◆ Anode 3,120 × 3,120 μm
- Recommended Wire Bond (Note 1)
 - ◆ Anode: 20 mil × 3

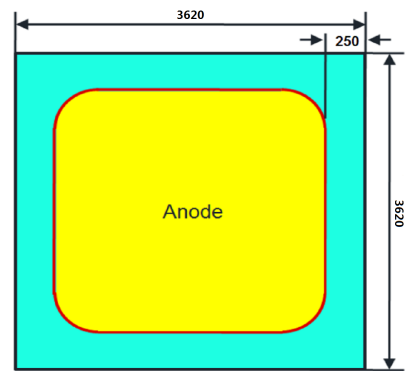
NOTE:

1. Based on TO-247 package of onsemi.



DIE LAYOUT

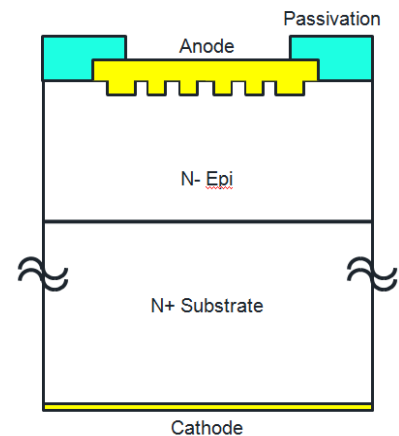
(Dimension: μm, Except Scribe Lane)



Passivation Information

- Passivation Material: Polyimide (PSPI)
- Passivation Type: Local Passivation
- Passivation Thickness: 90KA

CROSS SECTION



ORDERING INFORMATION

Part Number	Package	Die Size
PCFFS30120AF	N/A	3,700 × 3,700 μm (Include Scribe Lane)

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ELECTRICAL CHARACTERISTICS ON WAFER ($T_C = 25^\circ\text{C}$ unless otherwise noted) (Note 2)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_R	Reverse Blocking Voltage	$I_R = 200 \mu\text{A}$, $T_C = 25^\circ\text{C}$	1200	-	-	V
V_F	Forward Voltage	$I_F = 30 \text{ A}$, $T_C = 25^\circ\text{C}$	1.20	-	1.75	V
I_R	Reverse Current	$V_R = 1200 \text{ V}$, $T_C = 25^\circ\text{C}$	-	-	200	μA

2. Tested 100% on wafer.

The Configuration of Chips (Based on 6" Wafer)

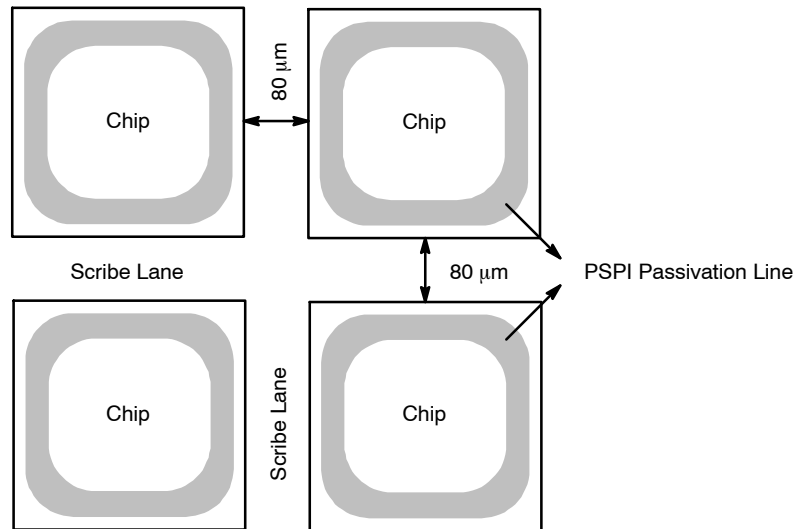


Figure 1. Saw-on-film Frame Packing Based on Tested Wafer

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	FFSH30120A	Unit	
V _{RRM}	Peak Repetitive Reverse Voltage	1200	V	
E _{AS}	Single Pulse Avalanche Energy (Note 3)	361	mJ	
I _F	Continuous Rectified Forward Current @ T _C < 155°C	30	A	
	Continuous Rectified Forward Current @ T _C < 135°C	46		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1500	A
		T _C = 150°C, 10 μs	1400	A
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	230	A
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	80	A
P _{tot}	Power Dissipation	T _C = 25°C	500	W
		T _C = 150°C	83	W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	
	TO247 Mounting Torque, M3 Screw	60	Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. E_{AS} of 361 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 38 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R _{θJC}	Thermal Resistance, Junction to Case, Max	0.3	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V _F	Forward Voltage	I _F = 30 A, T _C = 25°C	-	1.45	1.75	V
		I _F = 30 A, T _C = 125°C	-	1.7	2.0	
		I _F = 30 A, T _C = 175°C	-	2.0	2.4	
I _R	Reverse Current	V _R = 1200 V, T _C = 25°C	-	-	200	μA
		V _R = 1200 V, T _C = 125°C	-	-	300	
		V _R = 1200 V, T _C = 175°C	-	-	400	
Q _C	Total Capacitive Charge	V = 800 V	-	175	-	nC
C	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1740	-	pF
		V _R = 400 V, f = 100 kHz	-	159	-	
		V _R = 800 V, f = 100 kHz	-	130	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

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TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

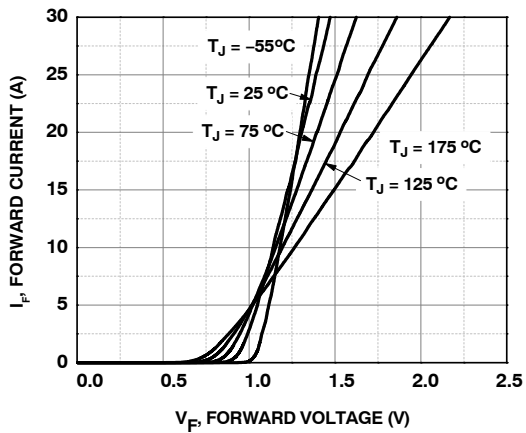


Figure 2. Forward Characteristics

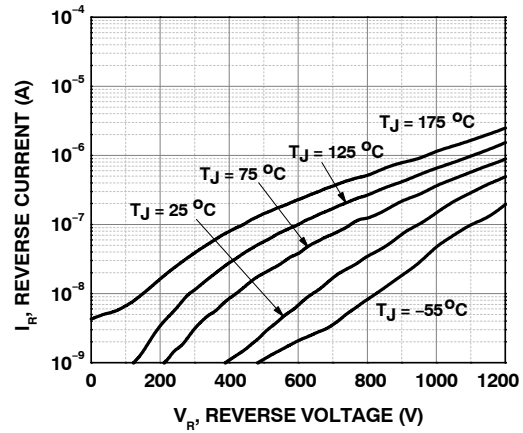


Figure 3. Reverse Characteristics

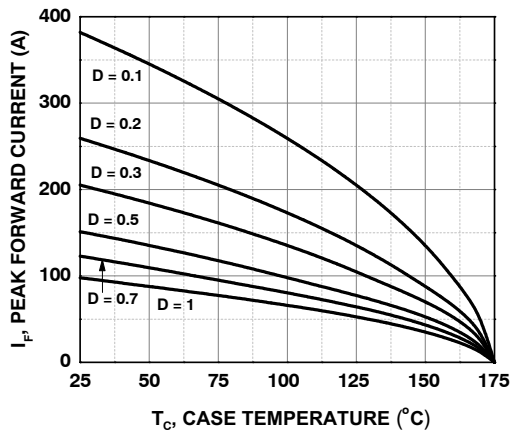


Figure 4. Current Derating

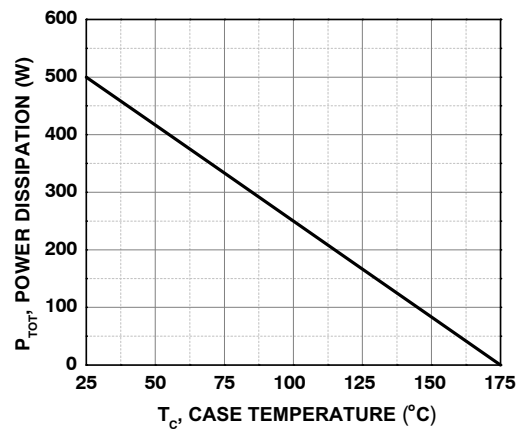


Figure 5. Power Derating

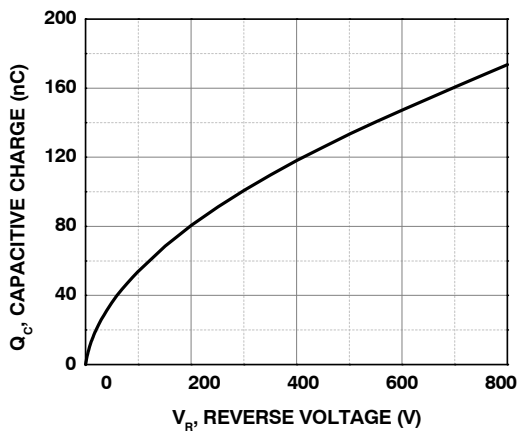


Figure 6. Capacitive Charge vs. Reverse Voltage

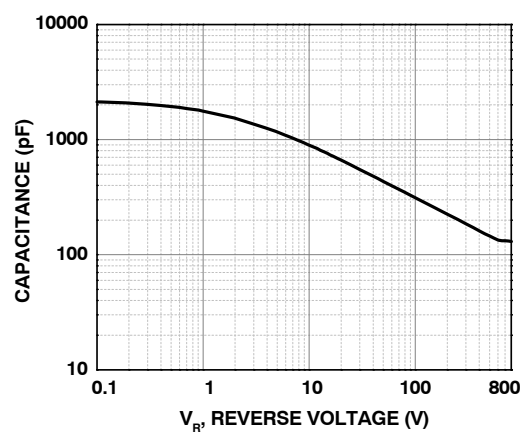


Figure 7. Capacitive vs. Reverse Voltage

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TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

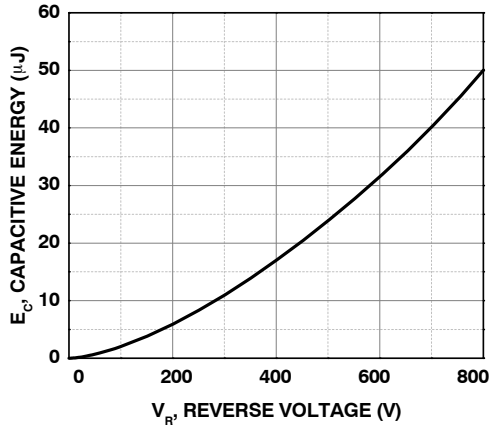


Figure 8. Capacitance Stored Energy

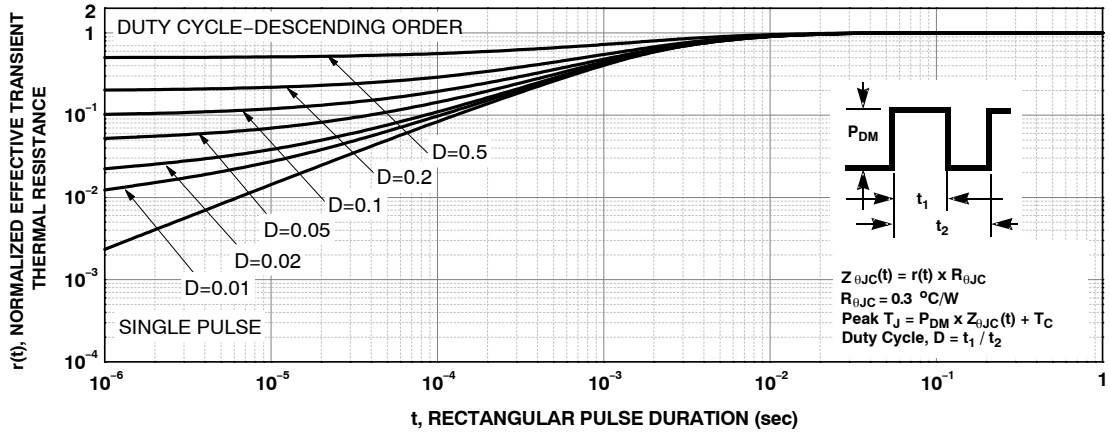


Figure 9. Junction-to-Case Transient Thermal Response Curve

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TEST CIRCUIT AND WAVEFORMS

$L = 0.5 \text{ mH}$
 $R < 0.1 \Omega$
 $V_{DD} = 50 \text{ V}$
 $E_{AVL} = 1/2LI^2 [V_{R(AVL)} / (V_{R(AVL)} - V_{DD})]$
 $Q1 = \text{IGBT} (BV_{CES} > \text{DUT } V_{R(AVL)})$

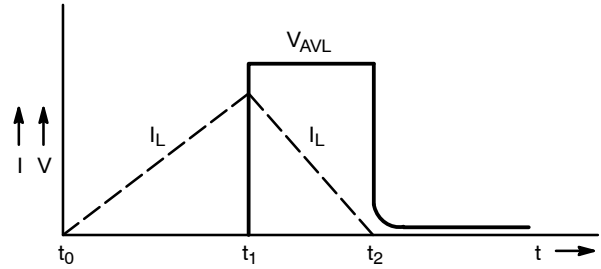
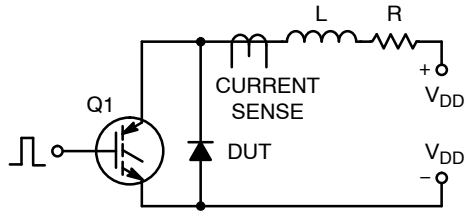


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform

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